

Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Electronic thermostats
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids
- Refrigeration and air conditioning compressors

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4; Fig. 5}$	-	-	140	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 45$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	16	A
Static charac	cteristics					,
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{7}$	2	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-T1
2	T2	main terminal 2		sym051
3	G	gate		
mb	n.c.	mounting base; isolated		
			$ \bigcup_{1 \ 2 \ 3} $	
			TO-220F (SOT186A)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BTA316X-800B	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A				
BTA316X-800B/L01	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A				
BTA316X-800B/L02	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A				

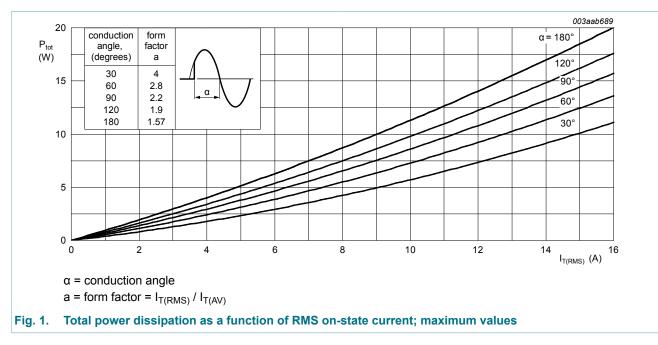
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7. Limiting values

Table 4.Limiting values

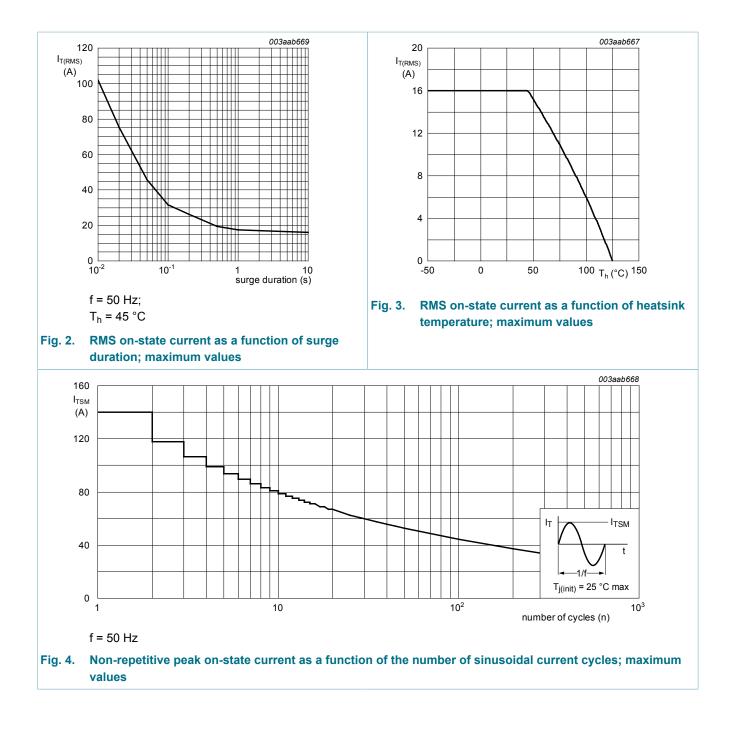
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 45 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	16	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	140	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 16.7 \text{ ms}$	-	150	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	98	A ² s
dI _T /dt	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs	-	100	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



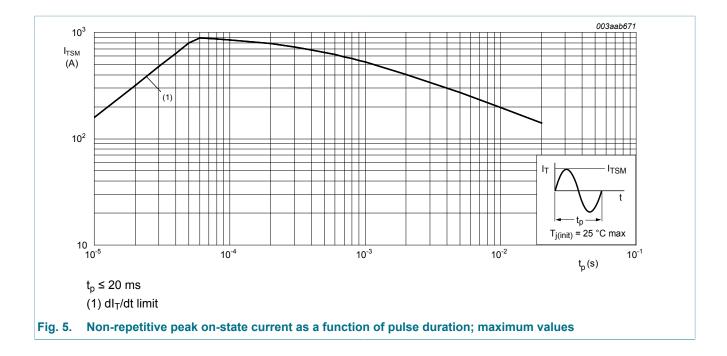
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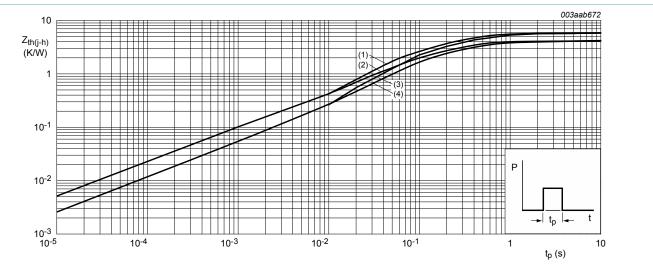
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8. Thermal characteristics

Table 5. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-h)}	thermal resistance from junction to	full cycle or half cycle; with heatsink compound; Fig. 6		-	-	4	K/W	
	heatsink	full cycle or half cycle; without heatsink compound; Fig. 6		-	-	5.5	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		-	55	-	K/W	



(1) Unidirectional (half cycle) without heatsink compound

(2) Unidirectional (half cycle) with heatsink compound

(3) Bidirectional (full cycle) without heatsink compound

(4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

9. Isolation characteristics

Table 6. Isolation characteristics									
Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C		-	-	2500	V		
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C		-	10	-	pF		

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	V_D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA
ΙL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	 -	-	60	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	 -	-	90	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	60	mA
lн	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	 -	-	60	mA
VT	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.8	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
ID	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 535 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 16 A; dV _{com} /dt = 20 V/µs; gate open circuit; without snubber	20	-	-	A/m
t _{gt}	gate-controlled turn-on time	I_{TM} = 20 A; V _D = 800 V; I _G = 0.1 A; dI _G / dt = 5 A/µs	-	2	-	μs

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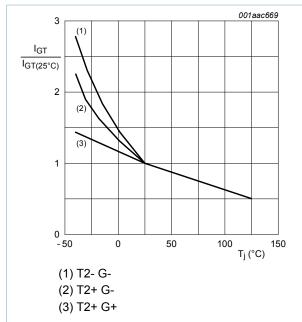


Fig. 7. Normalized gate trigger current as a function of junction temperature

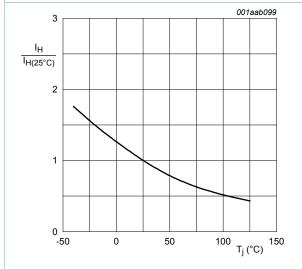
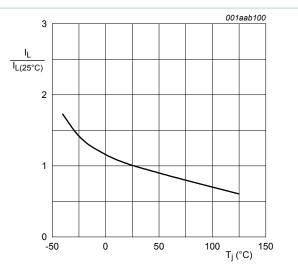
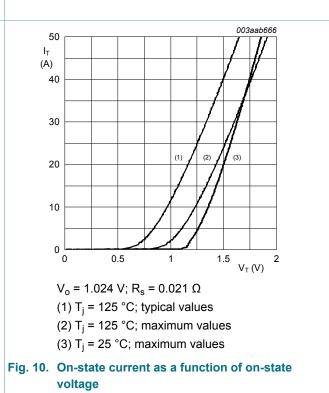


Fig. 9. Normalized holding current as a function of junction temperature

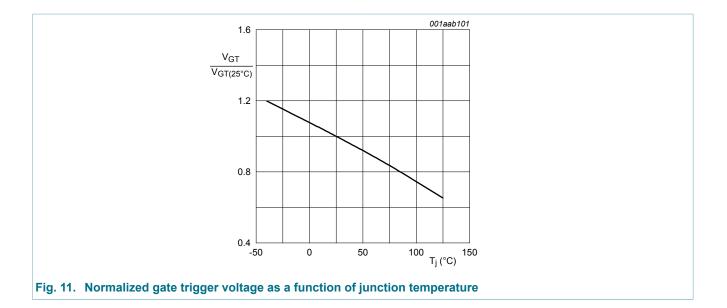






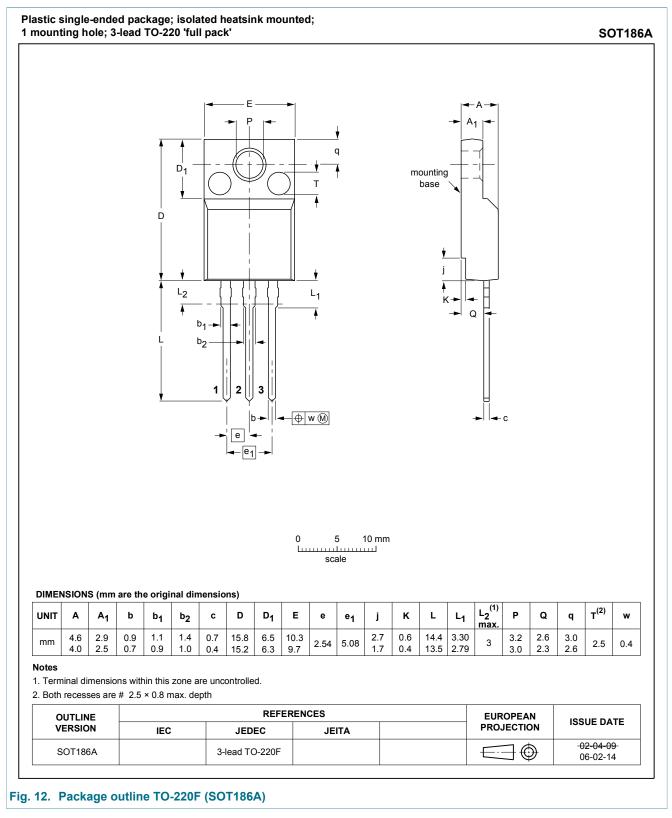
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11. Package outline



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